

## Features

- Low drain-source on-resistance:  $R_{DS(ON)}=0.074\Omega(\text{typ})$
- Very Low FOM ( $R_{DS(on)} \times Q_g$ )
- Extremely low switching loss
- 100% avalanche tested
- RoHS compliant

## Key Performance Parameters



Parameter	Value	Unit
$V_{DS} @ T_{j,\max}$	600	V
$R_{DS(ON),\max}$	82	mΩ
$I_D$	47	A
$Q_{g,\text{typ}}$	72	nC
$I_{DM}$	141	A

## Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



## Absolute Maximum Ratings( $T_c=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	TO-220F	TO-247	Unit
Drain-Source Voltage	$V_{DS}$	600		V
Gate-Source Voltage	$V_{GS}$		$\pm 30$	V
Continuous Drain Current <sup>1</sup>	$I_D$	47		A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	141		A
Single Pulse Avalanche Energy <sup>4</sup>	$E_{AS}$	1280		mJ
Avalanche Current	$I_{AS}$	10.5		A
Repetitive Avalanche Energy	$E_{AR}$	1.7		mJ
MOSFET dv/dt ruggedness, $V_{DS} = 0\dots 400\text{V}$	dv/dt	50		V/ns
Reverse diode dv/dt <sup>3</sup> $V_{DS}=0\dots 400\text{V}$ , $I_{SD} \leq I_D$		50		
Total Power Dissipation ( $T_c=25^\circ\text{C}$ )	$P_D$	40	391	W
Storage Temperature Range	$T_{STG}$	-55 to 150		°C
Operating Junction Temperature Range	$T_J$	-55 to 150		°C

## Thermal Characteristics

Parameter	Symbol	TO-220F	TO-247	Unit
Thermal Resistance Junction-Ambient (Max)	$R_{\theta JA}$	80	62	°C/W
Thermal Resistance Junction-Case (Max)	$R_{\theta JC}$	3	0.32	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	600	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=23.5\text{A}$	---	74	82	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D=1.24\text{mA}$	2.5	3.5	4.5	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=600\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
		$V_{\text{DS}}=600\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=150^\circ\text{C}$	---	---	100	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GS}}$	$V_{\text{GS}}=\pm 30\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	$\text{nA}$
Gate Resistance	$R_g$	$V_{\text{DS}}=0\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	1.95	---	$\Omega$
Total Gate Charge	$Q_g$	$V_{\text{DD}}=480\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=47\text{A}$	---	72	---	$\text{nC}$
Gate-Source Charge	$Q_{\text{gs}}$		---	14	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	24	---	
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DD}}=400\text{V}$ , $R_G=1.9\Omega$ , $I_D=25.8\text{A}$ , $V_{\text{GS}}=13\text{V}$	---	15	---	$\text{ns}$
Rise Time	$T_r$		---	12	---	
Turn-Off Delay Time	$T_{\text{d(off)}}$		---	80	---	
Fall Time	$T_f$		---	6	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=50\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	3680	---	$\text{pF}$
Output Capacitance	$C_{\text{oss}}$		---	390	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	15	---	

**Drain-Source Diode Characteristics**

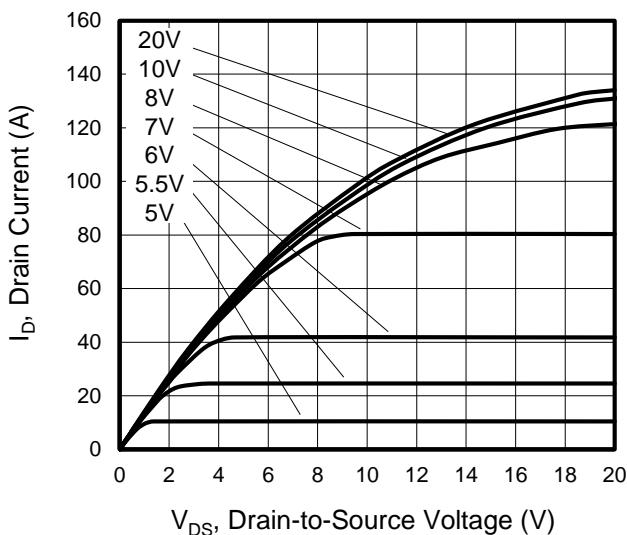
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current	$I_s$	$T_c=25^\circ\text{C}$	---	---	47	A
Pulsed Source Current	$I_{\text{SM}}$		---	---	141	A
Diode Forward Voltage	$V_{\text{SD}}$	$V_G=0\text{V}$ , $I_s=47\text{A}$ , $T_J=25^\circ\text{C}$	---	0.9	1.2	V
Reverse Recovery Time	$t_{\text{rr}}$	$V_R=400\text{V}$ , $I_F=25.8\text{ A}$ , $dI_F/dt=100\text{A}/\mu\text{s}$	---	518	---	$\text{ns}$
Reverse Recovery Charge	$Q_{\text{rr}}$		---	8	---	$\text{uC}$
Peak Reverse Recovery Current	$I_{\text{rrm}}$		---	26	---	A

**Note:**

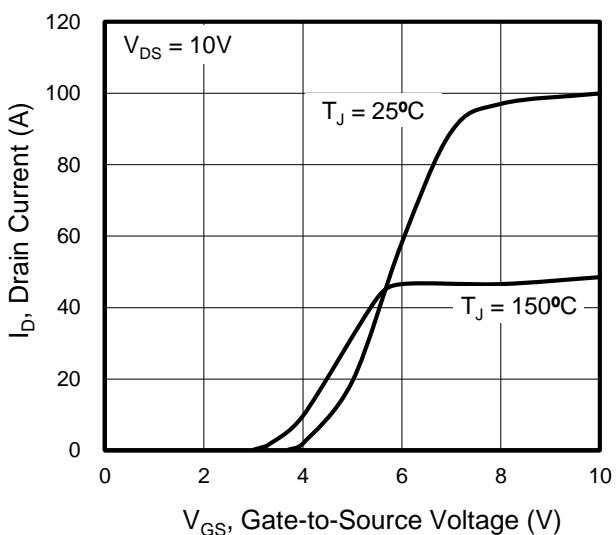
1. Limited by  $T_{j,\text{max}}$ . Maximum Duty Cycle D = 0.50
2. Pulse width  $t_p$  limited by  $T_{j,\text{max}}$
3. Identical low side and high side switch with identical  $R_g$
4.  $V_{\text{DD}}=50\text{V}$ ,  $R_g=25\Omega$ ,  $I_{\text{AS}}=10.5\text{A}$ , Starting  $T_J=25^\circ\text{C}$

## Typical Characteristics

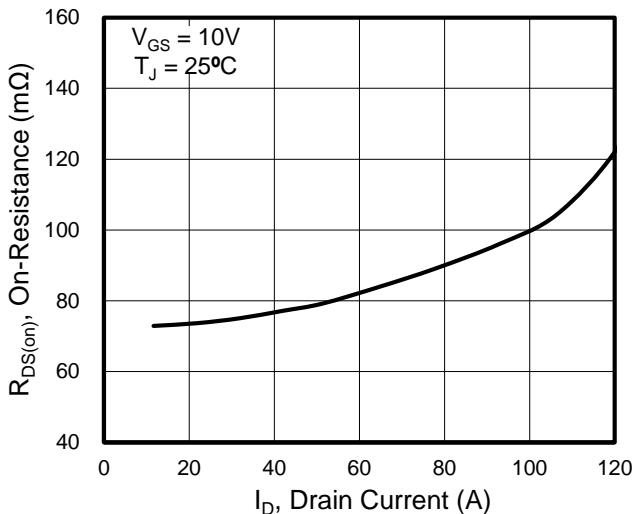
**Figure 1. Output Characteristics**



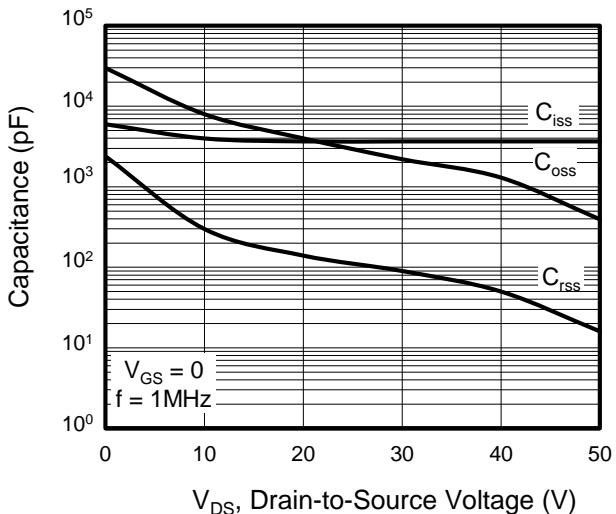
**Figure 2. Transfer Characteristics**



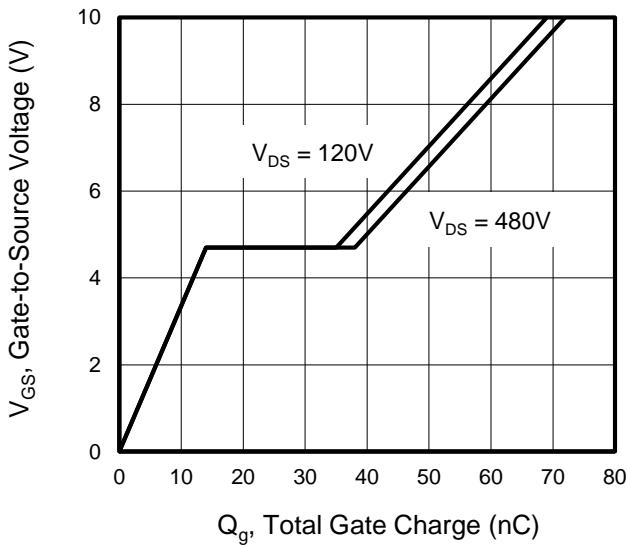
**Figure 3. On-Resistance vs. Drain Current**



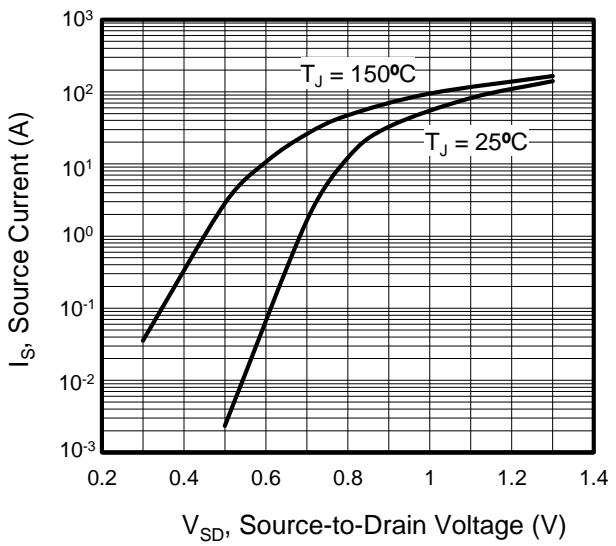
**Figure 4. Capacitance**

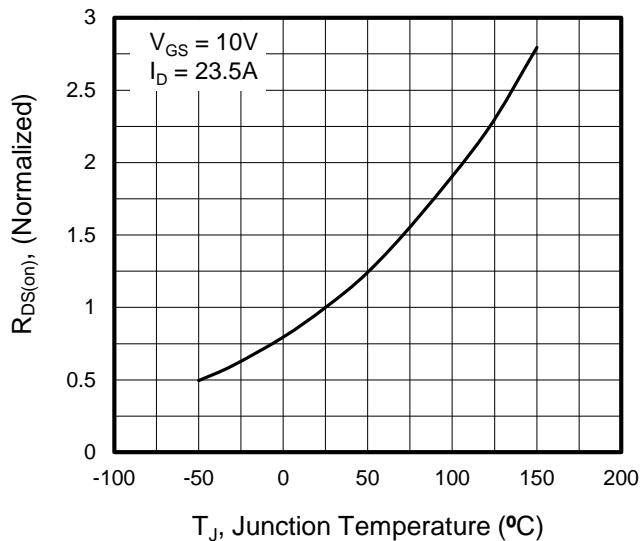
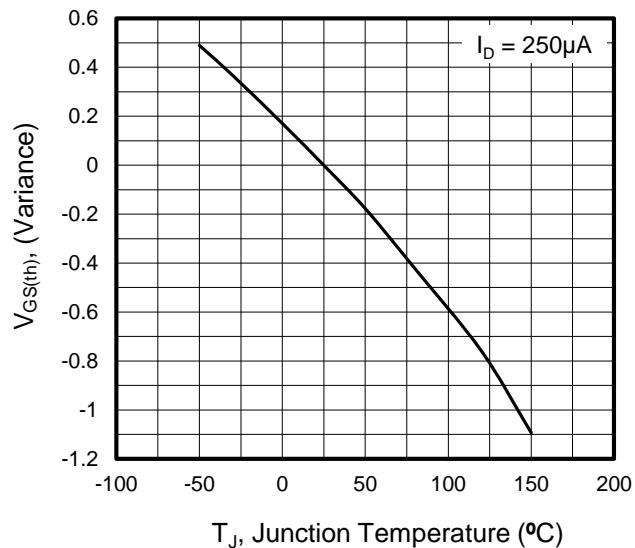
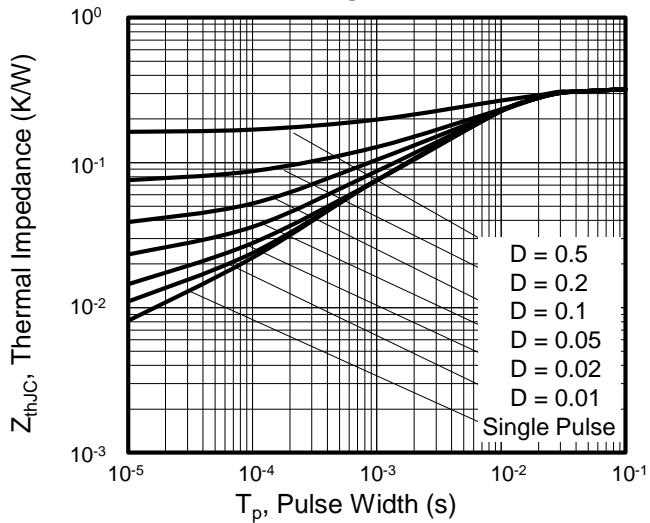
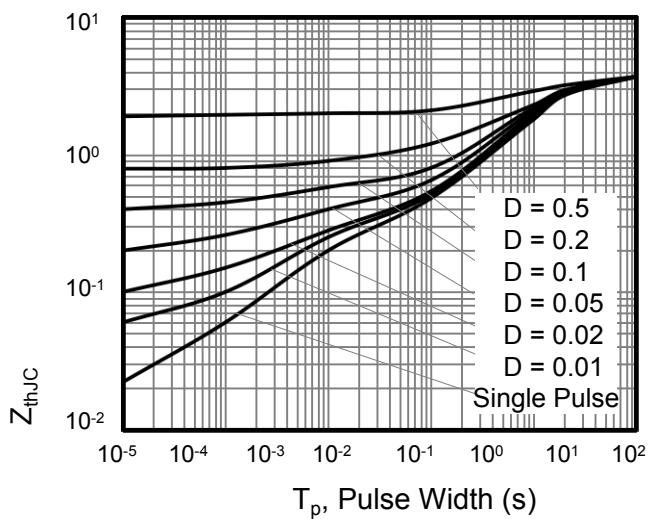


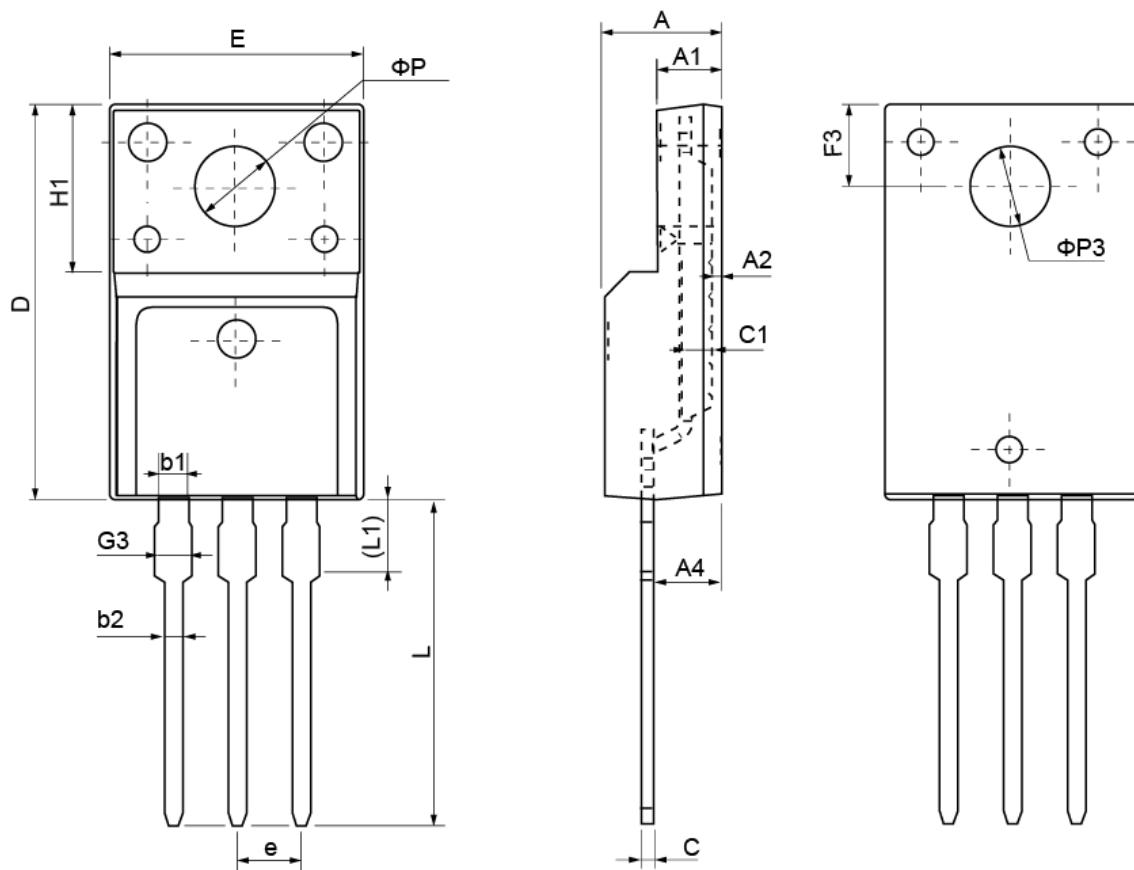
**Figure 5. Gate Charge**



**Figure 6. Body Diode Forward Voltage**

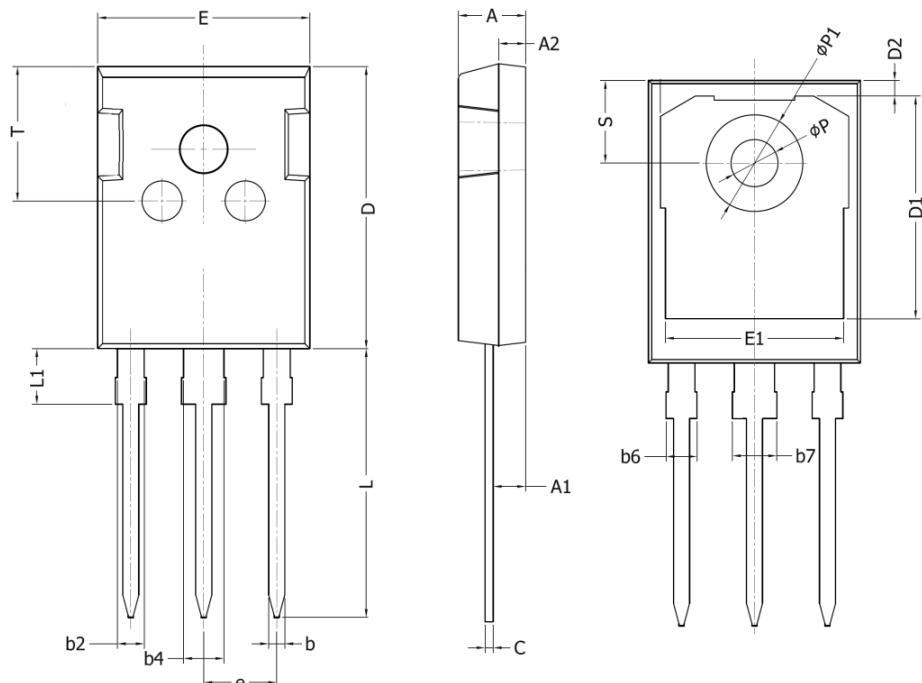


**Figure 7. On-Resistance vs. Temperature**

**Figure 8. Threshold Voltage vs. Temperature**

**Figure 9. Transient Thermal Impedance  
TO-247**

**Figure 10. Transient Thermal Impedance  
TO-220F**


**TO-220F Package Outline Dimensions**


<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	4.40	4.70	5.00	<b>H1</b>	6.70 REF		
<b>A1</b>	2.30	2.55	2.80	<b>L</b>	12.30	12.98	13.30
<b>A2</b>	0.30	0.50	0.70	<b>L1</b>	2.95	3.10	3.50
<b>A4</b>	2.45	2.80	3.05	<b>φ P</b>	3.03	3.20	3.50
<b>c</b>	0.30	0.50	0.70	<b>φ P3</b>	3.15	3.45	3.65
<b>c1</b>	1.20	1.30	1.40	<b>b1</b>	1.10	1.30	1.45
<b>D</b>	15.40	15.90	16.40	<b>b2</b>	0.60	0.80	1.00
<b>E</b>	9.86	10.16	10.46	<b>F3</b>	3.05	3.30	3.55
<b>e</b>	2.54 BSC			<b>G3</b>	1.15	1.35	1.55

### TO-247 Package Outline Dimensions



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.90	5.20
A1	2.31	2.51
A2	1.9	2.1
b	1.16	1.26
b2	1.96	2.06
b4	2.96	3.06
b6	-	2.25
b7	-	3.25
C	0.59	0.66
D	20.90	21.20
D1	16.25	16.85
D2	1.05	1.35
E	15.75	16.10
E1	13.00	13.60
e	5.436 BSC	
L	19.80	20.20
L1	-	4.30
P	3.40	3.60
P1	7.00	7.40
S	6.05	6.25
T	9.80	10.20